

Table 1

# PBSS306PZ

100 V, 4.1 A PNP low VCEsat (BISS) transistor Rev. 3 — 26 July 2011

Product data sheet

#### 1. **Product profile**

### 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS306NZ.

### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FF</sub>) at high I<sub>C</sub>

### 1.3 Applications

Quick reference data

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control

### 1.4 Quick reference data

- High efficiency due to less heat generation
- Smaller Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

Table 1.	QUICK reference uata					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-100	V
I <sub>C</sub>	collector current		-	-	-4.1	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	-8.2	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	56	80	mΩ

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# 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		- <i>i</i>
2	С	collector		2,4
3	Е	emitter		1
4	С	collector		
			SOT223 (SC-73)	3 sym028

# 3. Ordering information

Table 3. Ordering	g information		
Type number	Package		
	Name	Description	Version
PBSS306PZ	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

### 4. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS306PZ	S306PZ

# 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-100	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-100	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-4.1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-8.2	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	0.7	W
			[2]	-	1.7	W
			[3]	-	2	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

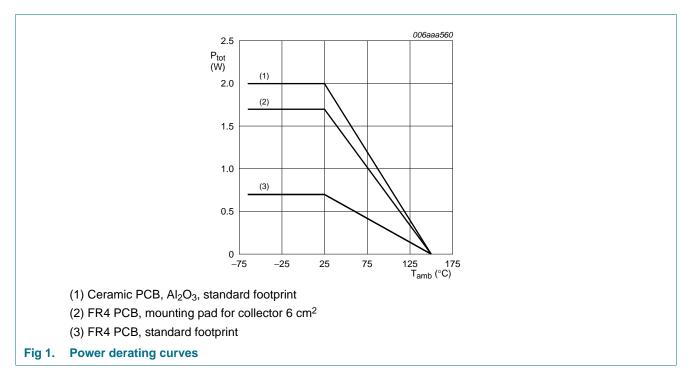
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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### 6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	179	K/W
			[2]	-	-	74	K/W
	amplem		[3]	-	-	63	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	15	K/W

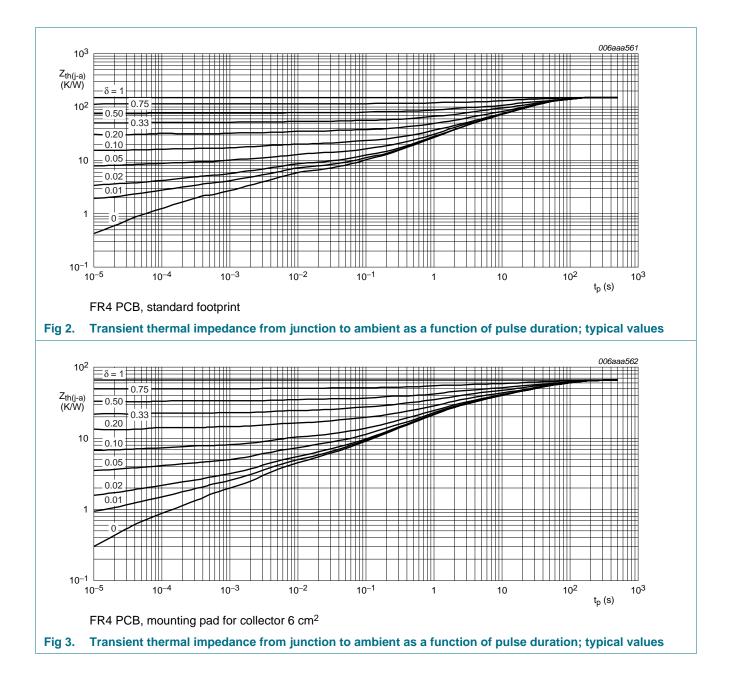
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

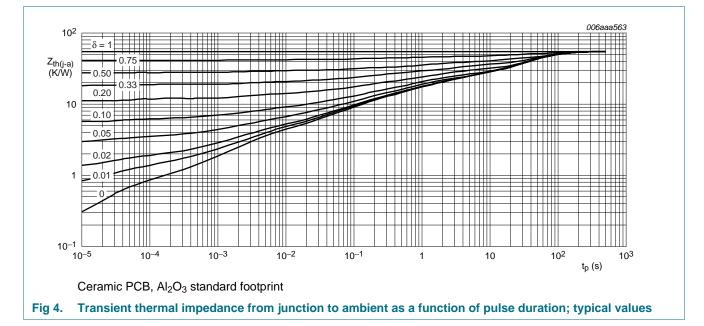
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#### 100 V, 4.1 A PNP low VCEsat (BISS) transistor



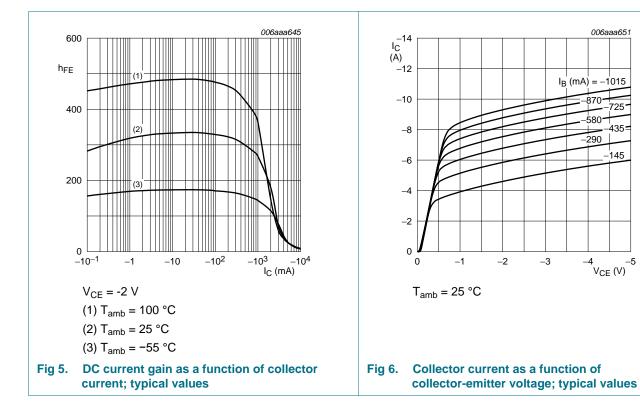
# 7. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -80 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	$V_{CB}$ = -80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C; T <sub>amb</sub> = 25 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -48 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$ \begin{aligned} &V_{CE} = \text{-2 V; } I_{C} = \text{-0.5 A; pulsed;} \\ &t_{p} \leq 300 \; \mu s; \; \delta \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ}C \end{aligned} $	200	300	-	
			150	260	-	
			100	175	-	
		$    V_{CE} = -2 \text{ V}; \text{ I}_{C} = -4 \text{ A}; \text{ pulsed};                                    $	25	40	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$ \begin{array}{l} I_{C} = -0.5 \text{ A}; \ I_{B} = -50 \text{ mA}; \ \text{pulsed}; \\ t_{p} \leq 300 \ \mu\text{s}; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}\text{C} \end{array} $	-	-45	-65	mV
		$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-90	-130	mV
		$    I_C = -4 \text{ A}; I_B = -400 \text{ mA}; \text{ pulsed};                                    $	-	-225	-320	mV
		$I_C$ = -4.1 A; $I_B$ = -410 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-230	-325	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$\begin{split} I_{C} &= -4 \text{ A};  I_{B} = -400 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \delta \leq 0.02 ;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	56	80	mΩ
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Table 7.						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>BEsat</sub>	base-emitter saturation voltage	$    I_C = -1 \text{ A}; I_B = -100 \text{ mA}; \text{ pulsed};                                    $	-	-0.81	-0.9	V
		$    I_C = -4 \text{ A}; I_B = -400 \text{ mA}; \text{ pulsed};                                    $	-	-0.93	-1.05	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$    V_{CE} = -2 \text{ V; } I_C = -2 \text{ A; pulsed;}                                    $	-	-0.78	-0.85	V
t <sub>d</sub>	delay time	$V_{CC}$ = -12.5 V; I <sub>C</sub> = -3 A; I <sub>Bon</sub> = -0.15 A;	-	15	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 0.15 A; T <sub>amb</sub> = 25 °C	-	185	-	ns
t <sub>on</sub>	turn-on time		-	200	-	ns
t <sub>s</sub>	storage time		-	150	-	ns
f	fall time		-	175	-	ns
off	turn-off time		-	325	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	100	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	50	80	pF



#### Table 7. Characteristics ... continued

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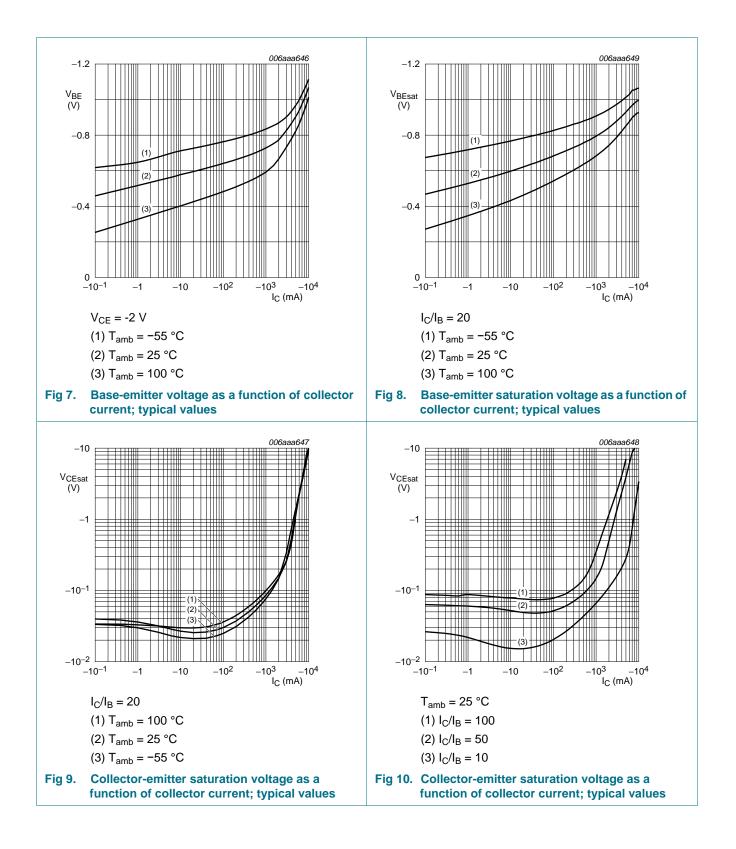
135

145

-5

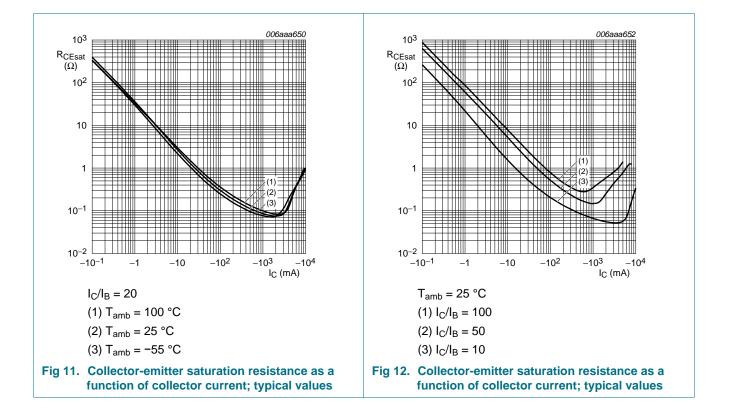
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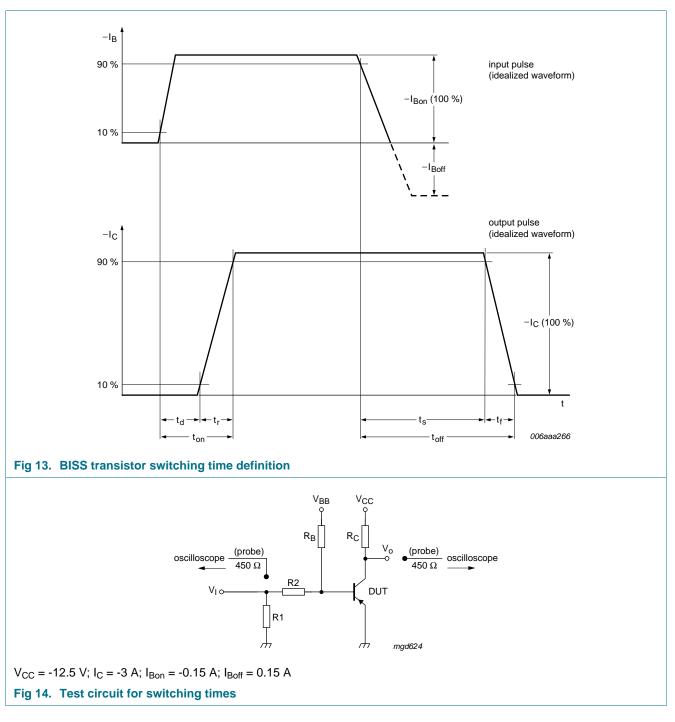
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#### 100 V, 4.1 A PNP low VCEsat (BISS) transistor

# 8. Test information



#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors and is suitable for use in automotive applications.

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### 9. Package outline

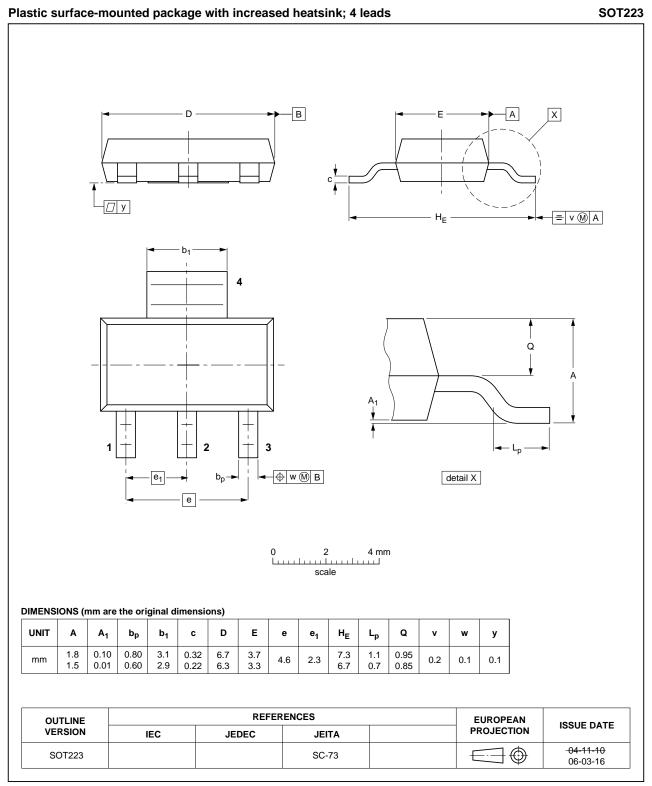
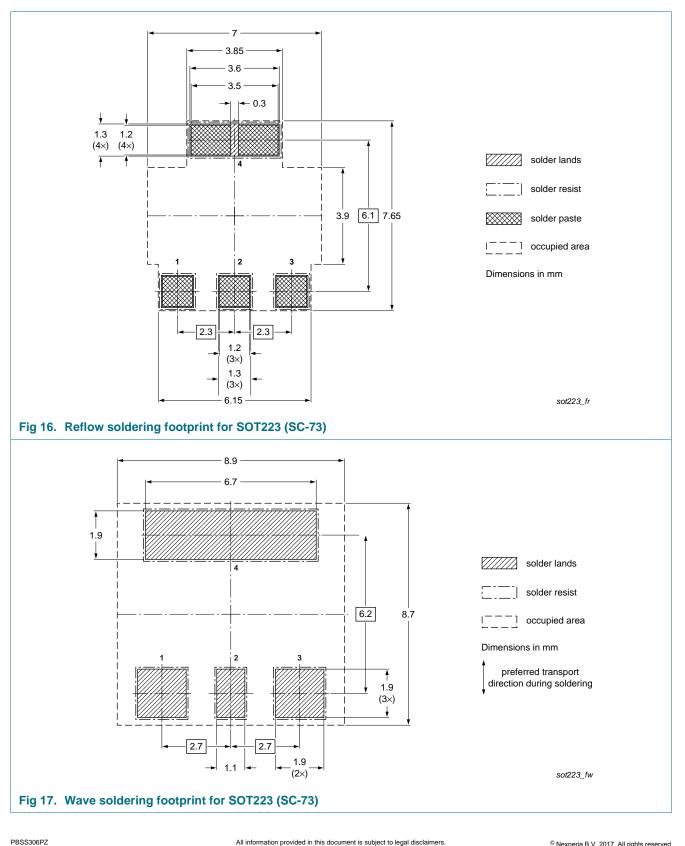


Fig 15. Package outline SOT223 (SC-73)

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# 10. Soldering



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# **11. Revision history**

Table 8. Revision	n history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS306PZ v.3	20110726	Product data sheet	-	PBSS306PZ v.2
Modifications:	In <u>7 "Charact</u> "	and benefits" updated reristics" new parameter adde	ed, I <sub>CES</sub>	
	<ul> <li>Fig 15. update</li> <li>12 "Legal info</li> </ul>	ted <u>prmation"</u> updated		
PBSS306PZ v.2	20091211	Product data sheet	-	PBSS306PZ v.1
PBSS306PZ v.1	20060920	Product data sheet	-	-

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# **12. Legal information**

#### **12.1 Data sheet status**

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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